

TECHNICAL DATA
DATA SHEET 606, REV. A
Formerly DS302, SHD2262

HERMETIC POWER MOSFET N-CHANNEL

FEATURES:

- 100 Volt, 0.092 Ohm, 18A MOSFET
- Isolated Hermetic Metal Package
- Fast Switching
- Low $R_{DS(on)}$
- Equivalent to IRFY140 Series
- Add Suffix 'C' to the Part Number for Ceramic Seals

MAXIMUM RATINGS

ALL RATINGS ARE AT $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

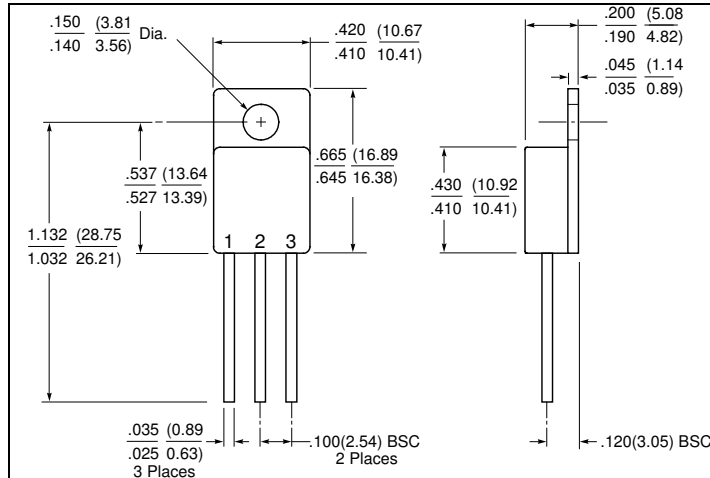
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
ON-STATE DRAIN CURRENT	I_D	-	-	18	Amps
	@ $T_C = 25^\circ\text{C}$				
	@ $T_C = 100^\circ\text{C}$	-	-	12	
PULSED DRAIN CURRENT	I_{DM}	-	-	72	Amps
	@ $T_C = 25^\circ\text{C}$				
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	$^\circ\text{C}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	P_D	-	-	60	Watts

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 1.0\text{mA}$	BV_{DSS}	100	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10\text{V}, I_D = 12\text{A}$	$R_{DS(ON)}$	-	-	0.092	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} \geq 15\text{V}, I_D = 12\text{A}$	g_{fs}	9.1	-	-	$\text{S}(1/\Omega)$
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 0.8 \times \text{Max. Rating}, V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \times \text{Max. Rating}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$	I_{DSS}	-	-	25 250	μA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20\text{V}$	I_{GSS}	-	-	100	nA
GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20\text{V}$				-100	
TURN ON DELAY TIME RISE TIME TURN OFF DELAY TIME FALL TIME $V_{DD} = 50\text{V}, I_D = 18\text{A}, R_G = 9.1\Omega, V_{GS} = 10\text{V}$	$t_{d(ON)}$ t_r $t_{d(OFF)}$ t_f	-	-	21 145 64 105	nsec
DIODE FORWARD VOLTAGE $T_C = 25^\circ\text{C}, I_S = 18\text{A}, V_{GS} = 0\text{V}$	V_{SD}	-	-	1.5	Volts
REVERSE RECOVERY TIME $T_J = 25^\circ\text{C}, I_S = 18\text{A}, di/ds = 100\text{A}/\mu\text{sec}, V_{DD} \leq 50\text{V}$	t_{rr}	-	-	400	nsec
INPUT CAPACITANCE OUTPUT CAPACITANCE REVERSE TRANSFER CAPACITANCE $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$	C_{iss} C_{oss} C_{rss}	-	1600 550 120	-	pF
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	2.1	$^\circ\text{C}/\text{W}$

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MECHANICAL DIMENSIONS: in Inches / mm



TO-257

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET TO-257 PACKAGE	DRAIN	SOURCE	GATE

TECHNICAL DATA

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